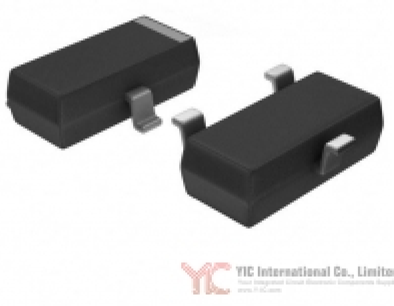


Image may be representation.
See specs for product details.

SI2351DS-T1-GE3

Hersteller-Teilenummer:	SI2351DS-T1-GE3
Hersteller / Marke:	Electro-Films (EFI) / Vishay
Teil der Beschreibung:	MOSFET P-CH 20V 2.8A SOT23-3
Datenblätter:	SI2351DS-T1-GE3.pdf
RoHs Status:	Bleifrei / RoHS-konform
Lagerzustand:	New original, 159163 pcs Stock Available.
Liefern von:	Hong Kong
Versandweg:	DHL/Fedex/TNT/UPS/EMS

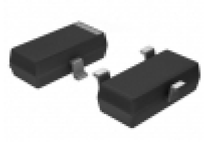
Spezifikationen

Teilenummer	SI2351DS-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET P-CH 20V 2.8A SOT23-3
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	159163 pcs Stock
detaillierte Beschreibung	P-Channel 20V 2.8A (Tc) 1W (Ta), 2.1W (Tc) Surface
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-236-3, SC-59, SOT-23-3
Supplier Device-Gehäuse	SOT-23-3 (TO-236)
Verlustleistung (max)	1W (Ta), 2.1W (Tc)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	2.8A (Tc)
Rds On (Max) @ Id, Vgs	115 mOhm @ 2.4A, 4.5V
VGS (th) (Max) @ Id	1.5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	5.1nC @ 5V
Eingabekapazität (Ciss) (Max) @ Vds	250pF @ 10V
Antriebsspannung (Max Rds On, Min Rds On)	2.5V, 4.5V
Vgs (Max)	±12V
Verpackung	Cut Tape (CT)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI2351DS-T1-GE3CT

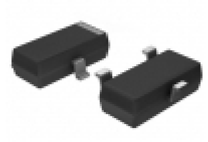
SI2351DS-T1-GE3 ist neu im Original, Suche SI2351DS-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI2351DS-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI2351DS-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

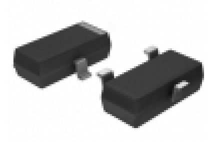
SI2365EDS
VISHAY
SI2365EDS VISHAY



SI2356DS-T1-GE3
Vishay / Siliconix
MOSFET N-CH 40V 4.3A SOT-23

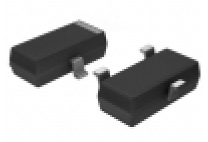


SI2351DS-T1-E3
Vishay / Siliconix
MOSFET P-CH 20V 2.8A SOT23-3



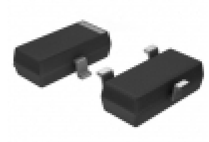
SI2356DS-T1-GE3
Electro-Films (EFI) / Vishay
MOSFET N-CH 40V 4.3A SOT-23

SI2356DS-T1-E3
VISHAY
VISHAY SOT-23



SI2351DS-T1-GE3
Vishay / Siliconix
MOSFET P-CH 20V 2.8A SOT23-3

SI2351DS
Vishay Precision Group
SI2351DS VISHAY



SI2347DS-T1-GE3
Electro-Films (EFI) / Vishay
MOSFET P-CH 30V 5A SOT-23

heiße Teile

Mehr

- SI2338DS-T1-E3
- SI2338DS-T1-GE3
- SI2338DS-T1-GE3
- SI2341DS
- SI2341DS-T1-E3
- SI2341DS-T1-E3
- SI2341DS-T1-GE3
- SI2341DS-T1-GE3
- SI2342DS-T1-E3
- SI2342DS-T1-GE3
- SI2342DS-T1-GE3
- SI2343ADS-T1-GE3
- SI2343CDS
- SI2343CDS-T1-E3
- SI2343CDS-T1-GE3
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- SI2347DS-T1-GE3
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- SI2356DS-T1-GE3
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- SI2365EDS
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- SI2372DS-T1-GE3
- SI2374DS-T1-GE3
- SI2374DS-T1-GE3
- SI2377DS-T1-GE3
- SI2377EDS
- SI2377EDS-T1-E3

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